TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74ACT74P, TC74ACT74F, TC74ACT74FN, TC74ACT74FT

DUAL D-TYPE FLIP FLOP WITH PRESET AND CLEAR

The TC74ACT74 is an advanced high speed CMOS D-FLIP FLOP fabricated with silicon gate and double - layer metal wiring C2MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

This device may be used as a level converter for interfacing TTL or NMOS to High Speed CMOS. The inputs are compatible with TTL, NMOS and CMOS output voltage

The signal level applied to the D INPUT is transferred to Q OUTPUT during the positive going transition of the CK pulse.

 $\overline{\text{CLR}}$ and $\overline{\text{PR}}$ are independent of the CK and are accomplished by setting the appropriate input to an "L" level. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES:

at $V_{CC} = 5V$

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- Low Power Dissipation ············· $I_{CC} = 4\mu A(Max.)$ at Ta = 25°C
- Compatible with TTL outputs $\cdots V_{1L} = 0.8V$ (Max.)

 $V_{1H} = 2.0V (Min.)$

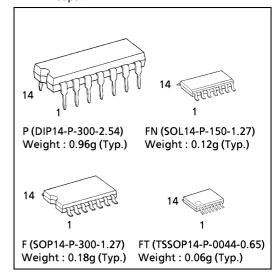
Symmetrical Output Impedance | I_{OH} | = I_{OL} = 24mA(Min.)

Capability of driving 50Ω

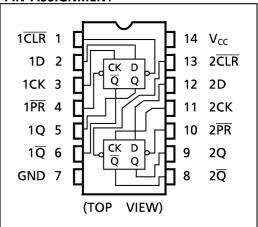
transmission lines.

- Balanced Propagation Delays ····· t_{pLH} ≃ t_{pHL}
- Pin and Function Compatible with 74F74

(Note) The JEDEC SOP (FN) is not available in Japan.



PIN ASSIGNMENT

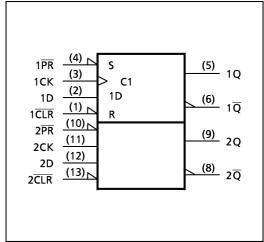


TRUTH TABLE

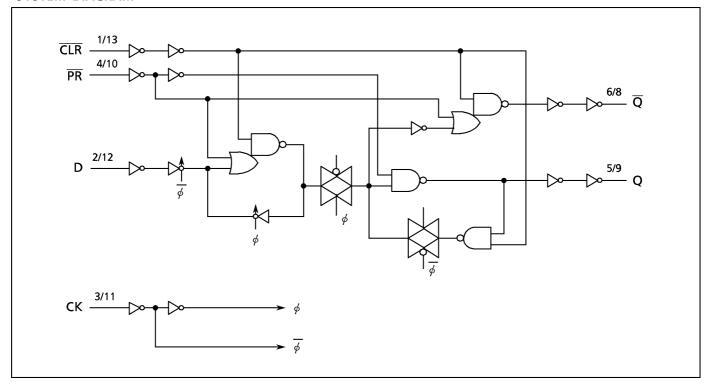
INPUTS				OUT	PUTS	FUNCTION	
CLR	PR	D	СК	Q	Q	FONCTION	
L	Н	Х	Х	L	Н	CLEAR	
Н	L	Х	Х	Н	L	PRESET	
L	L	Х	Х	Н	Н	_	
Н	Н	L	<u>_</u>	L	Н	_	
Н	Н	Н	<u>_</u>	Н	L		
Н	Н	Х	Į.	Qn	\overline{Q}_n	NO CHANGE	

X: Don't Care

IEC LOGIC SYMBOL



SYSTEM DIAGRAM



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V _{cc}	-0.5~7.0	V
DC Input Voltage	V _{IN}	-0.5~V _{CC} +0.5	V
DC Output Voltage	V _{OUT}	-0.5~V _{CC} +0.5	٧
Input Diode Current	I _{IK}	± 20	mA
Output Diode Current	I _{OK}	± 50	mA
DC Output Current	I _{OUT}	± 50	mΑ
DC V _{CC} /Ground Current	I _{CC}	± 100	mΑ
Power Dissipation	P _D	500 (DIP)* / 180 (SOP/TSSOP)	mW
Storage Temperature	T _{stg}	−65~150	°C

*500mW in the range of Ta = -40° C ~65°C. From Ta = 65°C to 85°C a derating factor of -10mW/°C should be applied up to 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	4.5~5.5	V
Input Voltage	V _{IN}	0~V _{cc}	V
Output Voltage	V _{OUT}	0~V _{CC}	V
Operating Temperature	Topr	−40~85	°C
Input Rise and Fall Time	dt/dV	0~10	ns / V

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION		V _{CC}	Ta = 25°C			Ta = -4	UNIT	
PARAIVIETER	STIVIBUL			(V)	MIN.	TYP.	MAX.	MIN.	MAX.	OIVIII
High - Level Input Voltage	V _{IH}			4.5 5.5	2.0	-	-	2.0	_	V
Low - Level Input Voltage	VIL			4.5 \$ 5.5	ı	-	0.8	-	0.8	V
High - Level Output Voltage	V _{OH}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -50 \mu A$ $I_{OH} = -24 m A$ $I_{OH} = -75 m A^*$	4.5 4.5 5.5	4.4 3.94 —	4.5 — —		4.4 3.80 3.85	_ _ _	V
Low - Level Output Voltage	V _{OL}	V _{IN} = V _{IH} or V _{IL}	$I_{OL} = 50 \mu A$ $I_{OL} = 24 m A$ $I_{OL} = 75 m A*$	4.5 4.5 5.5	111	0.0 — —	0.1 0.36 —	111	0.1 0.44 1.65	V
Input Leakage Current	I _{I N}	$V_{IN} = V_{CC}$ or GND		5.5	1	١	± 0.1	1	± 1.0	
	I _{cc}	$V_{IN} = V_{CC}$ or GN	ID	5.5			4.0	-	40.0	μΑ
Quiescent Supply Current	I _C	PER INPUT : V _{II} OTHER INPUT	$V_{CC} = 3.4V$: V_{CC} or GND	5.5	_		1.35	_	1.5	mA

^{* :} This spec indicates the capability of driving 50Ω transmission lines. One output should be tested at a time for a 10ms maximum duration.

TIMING REQUIREMENTS (Input $t_r = t_f = 3ns$)

PARAMETER	CYMPOL	TEST CONDI	TION	Ta = 25°C	Ta = −40~85°C	UNIT
PARAIVIETER	SYMBOL		V _{cc}	LIMIT	LIMIT	UNIT
Minimum Pulse Width (CK)	t _{W (L)} t _{W (H)}		5.0 ± 0.5	5.0	5.0	
Minimum Pulse Width (CLR, PR)	t _{W (L)}		5.0 ± 0.5	5.7	6.5	
Minimum Set-up Time	t _s		5.0 ± 0.5	3.5	3.5	ns
Minimum Hold Time	t _h		5.0 ± 0.5	1.5	1.5	
Minimum Removal Time (CLR, PR)	t _{rem}		5.0 ± 0.5	2.0	2.0	

AC ELECTRICAL CHARACTERISTICS (C_L = 50pF , $\,R_L$ = 500 Ω , Input $\,t_r$ = t_f = 3ns)

PARAMETER	SYMBOL	TEST CONDITION		•	Ta = 25°C		Ta = −40~85°C		UNIT
FARAIVIETER	STIVIBOL		V _{cc} (V)	MIN.	TYP.	MAX.	MIN.	MAX.	ONIT
Propagation Delay Time $(CK-Q,\overline{Q})$	t _{pLH} t _{pHL}		5.0 ± 0.5	_	6.1	9.2	1.0	10.5	ns
Propagation Delay Time $(\overline{CLR}, \overline{PR} - Q, \overline{Q})$	t _{pLH} t _{pHL}		5.0 ± 0.5	_	6.5	10.1	1.0	11.5	113
Maximum Clock Frequency	f _{MAX}		5.0 ± 0.5	95	160	_	95	_	MHz
Input Capacitance	C _{IN}			_	5	10	_	10	
Power Dissipation Capacitance	C _{PD} (1)			_	35	_	_	_	pF

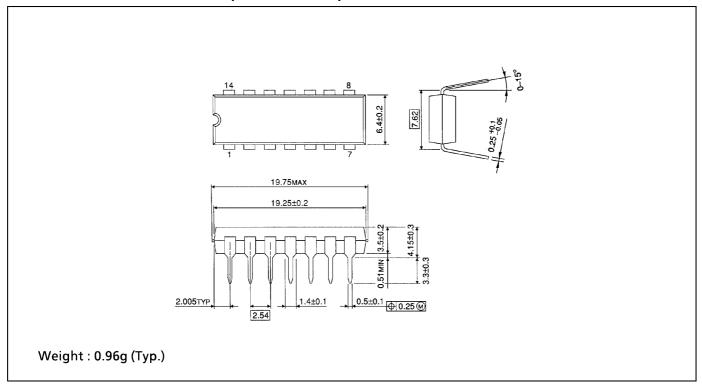
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC}(opr.) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2 (per F/F)$$

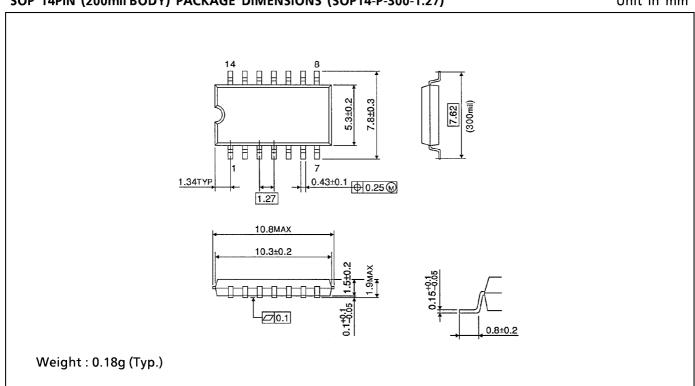
DIP 14PIN PACKAGE DIMENSIONS (DIP14-P-300-2.54)

Unit in mm



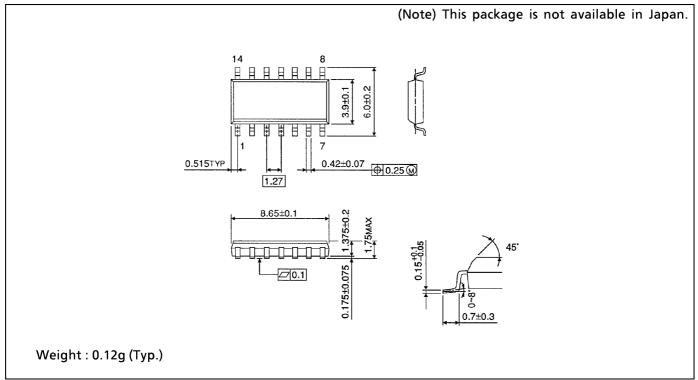
SOP 14PIN (200mil BODY) PACKAGE DIMENSIONS (SOP14-P-300-1.27)

Unit in mm



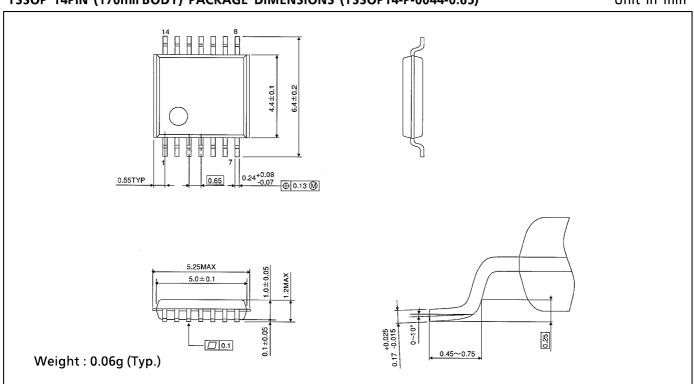
SOP 14PIN (150mil BODY) PACKAGE DIMENSIONS (SOL14-P-150 -1.27)

Unit in mm



TSSOP 14PIN (170mil BODY) PACKAGE DIMENSIONS (TSSOP14-P-0044-0.65)

Unit in mm



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